

Listing of Claims:

Claim 1 (Previously presented) A method for reducing line edge roughness of patterned photoresist, comprising:

providing a patterned photoresist, said patterned photoresist having at least a trench; and

filling said trenches, said trenches being totally filled by an additional material being effective attached to said patterned photoresist.

wherein a method for filling said trenches is dip.

Claim 2-7 (Canceled)

Claim 8 (Original) The method of claim 1, said additional material being a fluid material.

Claim 9 (Original) The method of claim 1, said additional material being chosen from the group consisting of solution and suspension.

Claim 10 (Original) The method of claim 1, said additional material being thermosetting polymer.

Claim 11 (Original) The method of claim 1, said additional material being thermoplasticity polymer.

Claim 12 (Previously presented) The method of claim 1, said additional material could be reacted with a hydroxyl group or proton of said patterned photoresist.

Claim 13 (Original) The method of claim 1, said additional material being chosen from the group consisting of PMMA, POLY IMIDE, RELACS, material with a plurality of -NH groups, and material with a plurality of -OH groups.

Claim 14 (Currently amended) The method of claim 1, further comprising treating said additional material to enhance the ~~so that~~ adhesion between said additional material and said patterned photoresist ~~is enhanced after said additional material is treated.~~

Claim 15-16 (Canceled)

Claim 17 (Previously presented) The method of claim 14, wherein available method for treating said additional material is chosen from the group consisting of thermal treatment, ultraviolet light curing, electrons beam curing, treatment of chemical reaction, and chemical reaction between a plurality of functional groups of said patterned photoresist and a plurality of functional groups of said additional materials.

Claim 18 (Previously presented) The method of claim 1, further comprising removing part of said additional material, removed part of said additional material being located on said patterned photoresist and said substrate.

Claim 19 (Canceled)

Claim 20 (Original) The method of claim 18, wherein

available method for removing part of said additional material is chosen from the group consisting of thermal treatment and spin.

Claim 21 (Previously presented) A method for reducing line edge roughness of patterned photoresist, comprising:

providing a patterned photoresist, said patterned photoresist having at least a trench; and

filling said trenches, said trenches being totally filled by an additional material being effective attached to said patterned photoresist,

wherein a method for filling said trenches is spray.

Claim 22 (Previously presented) The method of claim 21, said additional material being a fluid material.

Claim 23 (Previously presented) The method of claim 21, said additional material being chosen from the group consisting of solution and suspension.

Claim 24 (Previously presented) The method of claim 21, said additional material being thermosetting polymer.

Claim 25 (Previously presented) The method of claim 21, said additional material being thermoplasticity polymer.

Claim 26 (Previously presented) The method of claim 21, said additional material could be reacted with a hydroxyl group or proton of said patterned photoresist.

Claim 27 (Previously presented) The method of claim 21, said additional material being chosen from the group consisting of PMMA, POLY IMIDE, RELACS, material with a plurality of -NH groups, and material with a plurality of -OH groups.

Claim 28 (Currently amended) The method of claim 21, further comprising treating said additional material to enhance the so let that adhesion between said additional material and said patterned photoresist is enhanced after said additional material is treated.

Claim 29 (Previously presented) The method of claim 28, wherein available method for treating said additional material is chosen from the group consisting of thermal treatment, ultraviolet light curing, electrons beam curing, treatment of chemical reaction, and chemical reaction between a plurality of functional groups of said patterned photoresist and a plurality of functional groups of said additional materials.

Claim 30 (Previously presented) The method of claim 21, further comprising removing part of said additional material, removed part of said additional material being located on said patterned photoresist and said substrate.

Claim 31 (Previously presented) The method of claim 30, wherein available method for removing part of said additional material is chosen from the group consisting of thermal treatment and spin.

Claim 32 (Previously presented) A method for reducing line edge roughness of patterned photoresist, comprising:

providing a patterned photoresist, said patterned photoresist having at least a trench; and

filling said trenches, said trenches being totally filled by an additional material being effective attached to said patterned photoresist,

wherein a method for filling said trenches is spin coating.

Claim 33 (Previously presented) The method of claim 32, said additional material being a fluid material.

Claim 34 (Previously presented) The method of claim 32, said additional material being chosen from the group consisting of solution and suspension.

Claim 35 (Previously presented) The method of claim 32, said additional material being thermosetting polymer.

Claim 36 (Previously presented) The method of claim 32, said additional material being thermoplasticity polymer.

Claim 37 (Previously presented) The method of claim 32, said additional material could be reacted with a hydroxyl group or proton of said patterned photoresist.

Claim 38 (Previously presented) The method of claim 32, said additional material being chosen from the group consisting of PMMA, POLY IMIDE, RELACS, material with a plurality of -NH groups, and material with a plurality of -OH groups.

Claim 39 (Currently amended) The method of claim 32, further comprising treating said additional material to enhance the so let that adhesion between said additional material and said patterned photoresist is enhanced after said additional material is treated.

Claim 40 (Previously presented) The method of claim 39, wherein available method for treating said additional material is chosen from the group consisting of thermal treatment, ultraviolet light curing, electrons beam curing, treatment of chemical reaction, and chemical reaction between a plurality of functional groups of said patterned photoresist and a plurality of functional groups of said additional materials.

Claim 41 (Previously presented) The method of claim 32, further comprising removing part of said additional material, removed part of said additional material being located on said patterned photoresist and said substrate.

Claim 42 (Previously presented) The method of claim 41, wherein available method for removing part of said additional material is chosen from the group consisting of thermal treatment and spin.